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REPLY UNDER 37 CFR 1.116 **EXPEDITED PROCEDURE TECHNOLOGY CENTER 2800**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: 10/709,776

Conf. No.: 3775

Filing Date: 05/27/2004

Art Unit: 2811

Applicant: William G. America

Examiner: Im, Junghwa M.

Title:

SEMICONDUCTOR DEVICE

Docket No.: FIS920040083US1

FORMED BY IN-SITU MODIFICATION

(IBMF-0058)

OF DIELECTRIC LAYER AND

RELATED METHODS

COMMISSIONER FOR PATENTS

DESTINATION FACSIMILE NUMBER: 571-273-8300

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After-Final Amendment in 09 pages

in the above identified application.

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Mail Stop AF Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

AFTER-FINAL AMENDMENT

Sir:

INTRODUCTORY COMMENTS I.

This paper is being filed in response to the Final Office Action dated June 05, 2006.

Please amend the above-referenced patent application as follows:

10/709,776

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